

# ZXMS6004FF 60V N-channel self protected enhancement mode Intellifet MOSFET

### **Summary**

Continuous drain source voltage	60 V
On-state resistance	500 m $\Omega$
Nominal load current (V <sub>IN</sub> = 5V)	1.3 A
Clamping energy	90mJ



SOT23F

S

IIN

Pinout - top view

D

### Description

The ZXMS6004FF is a self protected low side MOSFET with logic level input. It integrates over-temperature, over-current, over-voltage (active clamp) and ESD protected logic level functionality. The ZXMS6004FF is ideal as a general purpose switch driven from 3.3V or 5V microcontrollers in harsh environments where standard MOSFETs are not rugged enough.

#### Features

- Compact high power dissipation package
- Low input current
- Logic Level Input (3.3V and 5V)
- · Short circuit protection with auto restart
- Over voltage protection (active clamp)
- · Thermal shutdown with auto restart
- Over-current protection
- Input Protection (ESD)
- High continuous current rating

### **Ordering information**

Device	Part mark	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMS66004FFTA	1K6	7	12 embossed	3,000 units

### Functional block diagram



## **Application information**

- Especially suited for loads with a high in-rush current such as lamps and motors.
- All types of resistive, inductive and capacitive loads in switching applications.
- $\mu C$  compatible power switch for 12V and 24V DC applications.
- Automotive rated.
- Replaces electromechanical relays and discrete circuits.
- Linear Mode capability the current-limiting protection circuitry is designed to de-activate at low  $V_{DS}$  to minimise on state power dissipation. The maximum DC operating current is therefore determined by the thermal capability of the package/board combination, rather than by the protection circuitry. This does not compromise the product's ability to self-protect at low  $V_{DS}$ .

## Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Continuous Drain-Source voltage	V <sub>DS</sub>	60	V
Drain-Source voltage for short circuit protection	V <sub>DS(SC)</sub>	36	V
Continuous input voltage	V <sub>IN</sub>	-0.5 +6	V
Continuous input current	I <sub>IN</sub>		mA
-0.2V≤V <sub>IN</sub> ≤6V		No limit	
V <sub>IN</sub> <-0.2V or V <sub>IN</sub> >6V		I <sub>IN</sub>  ≤2	
Operating temperature range	T <sub>j</sub> ,	-40 to +150	°C
Storage temperature range	T <sub>stg</sub>	-55 to +150	°C
Power dissipation at $T_A = 25^{\circ}C^{(a)}$	P <sub>D</sub>	0.83	W
Linear derating factor		6.66	mW/°C
Power dissipation at T <sub>A</sub> =25°C <sup>(b)</sup>	P <sub>D</sub>	1.5	W
Linear derating factor		12.0	mW/°C
Pulsed drain current @ V <sub>IN</sub> =3.3V	I <sub>DM</sub>	2	А
Pulsed drain current @ V <sub>IN</sub> =5V	I <sub>DM</sub>	2.5	А
Continuous source current (Body Diode) <sup>(a)</sup>	۱ <sub>S</sub>	1	А
Pulsed dource current (Body Diode)	I <sub>SM</sub>	5	А
Unclamped single pulse inductive energy,	E <sub>AS</sub>	90	mJ
Tj=25°C, I <sub>D</sub> =0.5A, V <sub>DD</sub> =24V			
Electrostatic discharge (Human body model)	V <sub>ESD</sub>	4000	V
Charged device model	V <sub>CDM</sub>	1000	V

### **Thermal resistance**

Parameter	Symbo	Value	Unit
Junction to ambient <sup>(a)</sup>	R <sub>θJA</sub>	150	°C/W
Junction to ambient <sup>(b)</sup>	R <sub>0JA</sub>	83	°C/W
Junction to case <sup>(c)</sup>	R <sub>θJC</sub>	44	°C/W

NOTES

(a) For a device surface mounted on a 15mm x 15mm single sided 1oz weight copper on 1.6mm FR4 board, in still air conditions.

(b) For a device surface mounted on 50mm x 50mm single sided 2oz weight copper on 1.6mm FR4 board in still air conditions.

(c) Thermal resistance from junction to the mounting surface of the drain pin.

### **Recommended operating conditions**

The ZXMS6004FF is optimised for use with  $\mu C$  operating from 3.3V and 5V supplies.

Symbol	Description	Min	Max	Units
V <sub>IN</sub>	Input voltage range	0	5.5	V
T <sub>A</sub>	Ambient temperature range	-40	125	°C
V <sub>IH</sub>	High level input voltage for MOSFET to be on	3	5.5	V
V <sub>IL</sub>	Low level input voltage for MOSFET to be off	0	0.7	V
V <sub>P</sub>	Peripheral supply voltage (voltage to which load is referred)	0	36	V

### Characteristics



Parameter	Symbol	Min	Тур	Мах	Unit	Conditions
Static Characteristics						
Drain-Source clamp voltage	V <sub>DS(AZ)</sub>	60	65	70	V	I <sub>D</sub> =10mA
Off-state drain Ccrrent	I <sub>DSS</sub>			500	nA	V <sub>DS</sub> =12V, V <sub>IN</sub> =0V
Off-state drain current	I <sub>DSS</sub>			1	μA	V <sub>DS</sub> =36V, V <sub>IN</sub> =0V
Input threshold voltage	V <sub>IN(th)</sub>	0.7	1	1.5	V	$V_{DS}=V_{GS}$ , $I_{D}=1mA$
Input current	I <sub>IN</sub>		60	100	μA	V <sub>IN</sub> =+3V
Input current	I <sub>IN</sub>		120	200	μA	V <sub>IN</sub> =+5V
Input current while over temperature active				220	μA	V <sub>IN</sub> =+5V
Static Drain-Source on-state resistance	R <sub>DS(on)</sub>		400	600	mΩ	V <sub>IN</sub> =+3V, I <sub>D</sub> =0.5A
Static Drain-Source on-state resistance	R <sub>DS(on)</sub>		350	500	mΩ	V <sub>IN</sub> =+5V, I <sub>D</sub> =0.5A
Continuous drain current <sup>(a)</sup>	I <sub>D</sub>	0.9			A	V <sub>IN</sub> =3V; T <sub>A</sub> =25°C
Continuous drain cCurrent (a)	I <sub>D</sub>	1.0			A	V <sub>IN</sub> =5V; T <sub>A</sub> =25°C
Continuous drain current <sup>(b)</sup>	I <sub>D</sub>	1.2			A	V <sub>IN</sub> =3V; T <sub>A</sub> =25°C
Continuous drain current <sup>(b)</sup>	I <sub>D</sub>	1.3			A	V <sub>IN</sub> =5V; T <sub>A</sub> =25°C
Current limit	I <sub>D(LIM)</sub>	0.7	1.7		A	V <sub>IN</sub> =+3V,
Current limit <sup>(c)</sup>	I <sub>D(LIM)</sub>	1	2.2		A	V <sub>IN</sub> =+5V
Dynamic characteristics						
Turn-on delay time	t <sub>d(on)</sub>		5		μs	V <sub>DD</sub> =12V, I <sub>D</sub> =0.5A,
Rise time	t <sub>r</sub>		10		μs	V <sub>GS</sub> =5V
Turn-off delay time	t <sub>d(off)</sub>		45		μs	]
Fall time	f <sub>f</sub>		15		μs	1

## Electrical characteristics (at $T_{amb} = 25^{\circ}C$ unless otherwise stated).

Notes:

(d) The drain current is restricted only when the device is in saturation (see graph 'typical output characteristic'). This allows the device to be used in the fully on state without interference from the current limit. The device is fully protected at all drain currents, as the low power dissipation generated outside saturation makes current limit unnecessary.

### **Electrical characteristics - continued**

Parameter	Symbol	Min	Тур	Max	Unit	Conditions
Over-temperature protection						
Thermal overload trip	TJT	150	175		°C	
temperature <sup>(a)</sup>						
Thermal hysteresis <sup>(a)</sup>			10		°C	

Note:

(a) Over-temperature protection is designed to prevent device destruction under fault conditions. Fault conditions are considered as "outside" normal operating range, so this part is not designed to withstand over-temperature for extended periods..

### **Typical characteristics**





**Typical Short Circuit Protection** 

10 Time (ms)

5

0

## Package information - SOT23F



Dim.	Millim	neters	Inc	hes	Dim. Millimeters Inches		Millimeters		hes
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
А	0.80	1.00	0.0315	0.0394	Е	2.30	2.50	0.0906	0.0984
A1	0.00	0.10	0.00	0.0043	E1	1.50	1.70	0.0590	0.0669
b	0.35	0.45	0.0153	0.0161	L	0.48	0.68	0.0189	0.0268
С	0.10	0.20	0.0043	0.0079	L1	0.30	0.50	0.0153	0.0161
D	2.80	3.00	0.1102	0.1181	R	0.05	0.15	0.0019	0.0059
е	0.95	ref	0.037	74 ref	0	0°	12°	0°	12°
e1	1.80	2.00	0.0709	0.0787	-	-	-	-	-

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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